General Purpose Transistors

NPN Silicon

These transistors are designed for general purpose amplifier applications. They are housed in the SC-75/SOT-416 package which is designed for low power surface mount applications.

Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- Pb–Free Packages are Available

MAXIMUM RATINGS ($T_A = 25^{\circ}C$)

Rating	Symbol	Мах	Unit
Collector-Emitter Voltage	V _{CEO}	45	V
Collector-Base Voltage	V _{CBO}	50	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current – Continuous	Ι _C	100	mAdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation, FR-4 Board (Note 1) $T_A = 25^{\circ}C$	P _D	200	mW
Derated above 25°C		1.6	mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	R_{\thetaJA}	600	°C/W
Total Device Dissipation, FR-4 Board (Note 2) $T_A = 25^{\circ}C$ Derated above $25^{\circ}C$	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ hetaJA}$	400	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	–55 to +150	°C

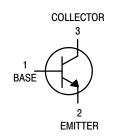
1. FR-4 @ min pad.

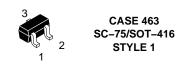
2. FR-4 @ 1.0 × 1.0 in pad.



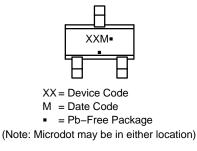
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MARKING DIAGRAM



ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

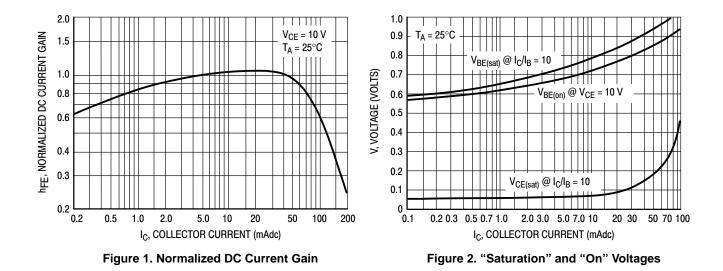
ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

(I_C = 0.2 mA, V_{CE} = 5.0 Vdc, R_S = 2.0 k\Omega, f = 1.0 kHz, BW = 200 Hz)

Characteristic	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS						•
Collector – Emitter Breakdown Voltage $(I_C = 10 \text{ mA})$	BC847 Series	V _{(BR)CEO}	45	_	_	V
Collector – Emitter Breakdown Voltage $(I_C = 10 \ \mu A, \ V_{EB} = 0)$	BC847 Series	V _{(BR)CES}	50	_	_	V
Collector – Base Breakdown Voltage $(I_C = 10 \ \mu A)$	BC847 Series	V _{(BR)CBO}	50	_	_	V
Emitter-Base Breakdown Voltage $(I_E = 1.0 \ \mu A)$	BC847 Series	V _{(BR)EBO}	6.0	_	_	V
Collector Cutoff Current (V _{CB} = 30 V) (V	_{CB} = 30 V, T _A = 150°C)	I _{CBO}	-		15 5.0	nA μA
ON CHARACTERISTICS		<u>.</u>				
DC Current Gain (I _C = 10 μ A, V _{CE} = 5.0 V)	BC847A BC847B BC847C	h _{FE}	- - -	90 150 270	- - -	_
$(I_{C} = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V})$	BC847A BC847B BC847C		110 200 420	180 290 520	220 450 800	
Collector Cutoff Current ($V_{CB} = 30 \text{ V}$) ($V_{CB} = 30 \text{ V}, T_A = 150^{\circ}\text{C}$) N CHARACTERISTICS DC Current Gain ($I_C = 10 \mu\text{A}, V_{CE} = 5.0 \text{ V}$) BC847A BC847B BC847C ($I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}$) BC847A BC847A BC847B BC847C Collector – Emitter Saturation Voltage ($I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$) ($I_C = 100 \text{ mA}, I_B = 5.0 \text{ mA}$) Base – Emitter Saturation Voltage ($I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$) ($I_C = 100 \text{ mA}, I_B = 5.0 \text{ mA}$) Base – Emitter Voltage ($I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}$) ($I_C = 100 \text{ mA}, I_B = 5.0 \text{ mA}$) Base – Emitter Voltage ($I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}$) ($I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$)		V _{CE(sat)}	-		0.25 0.6	V
	V _{BE(sat)}	-	0.7 0.9	_ _	V	
	V _{BE(on)}	580 -	660 -	700 770	mV	
SMALL-SIGNAL CHARACTERISTICS				•	•	•
Current-Gain – Bandwidth Product ($I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ Vdc}, f = 100 \text{ MHz}$)		f _T	100	-	_	MHz
Output Capacitance (V_{CB} = 10 V, f = 1.0 MHz)		C _{obo}	_	-	4.5	pF
Noise Figure $(1 - 0.2 \text{ m})/(1 - 5.0)/(1 - 5.$		NF			10	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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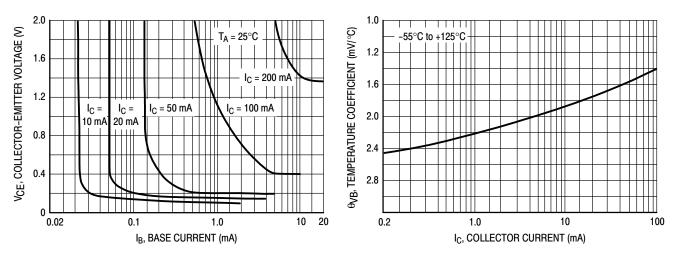


Figure 3. Collector Saturation Region



BC847

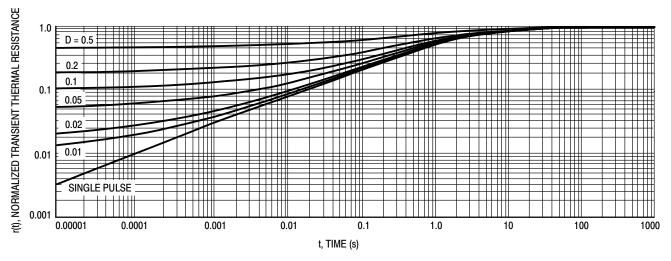
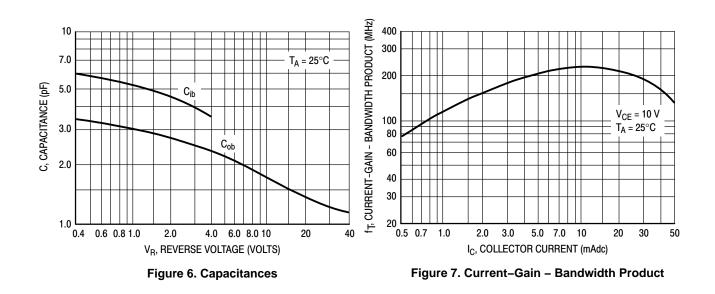


Figure 5. Normalized Thermal Response



ORDERING INFORMATION

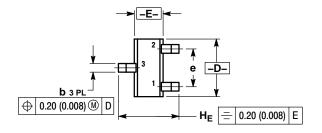
Device	Marking	Package	Shipping [†]
BC847ATT1	1E	SC-75/SOT-416	3,000 / Tape & Reel
BC847BTT1	1F	SC-75/SOT-416	
BC847BTT1G	1F	SC-75/SOT-416 (Pb-Free)	3,000 / Tape & Reel
NSVBC847BTT1G*	1F	SC-75/SOT-416 (Pb-Free)	3,000 / Tape & Reel
BC847CTT1G	1G	SC-75/SOT-416 (Pb-Free)	3,000 / Tape & Reel

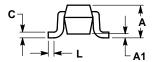
+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. *NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP

Capable.

PACKAGE DIMENSIONS

SC-75/SOT-416 CASE 463 ISSUE F





NOTES:

 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.70	0.80	0.90	0.027	0.031	0.035	
A1	0.00	0.05	0.10	0.000	0.002	0.004	
b	0.15	0.20	0.30	0.006	0.008	0.012	
С	0.10	0.15	0.25	0.004	0.006	0.010	
D	1.55	1.60	1.65	0.059	0.063	0.067	
E	0.70	0.80	0.90	0.027	0.031	0.035	
е	1.00 BSC			0.04 BSC			
L	0.10	0.15	0.20	0.004	0.006	0.008	
HE	1.50	1.60	1.70	0.061	0.063	0.065	

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